



High-Speed CMOS Bus Interface 10-Bit Buffers

QS54/74FCT827T
QS54/74FCT828T
QS54/74FCT2827T
QS54/74FCT2828T

FEATURES/BENEFITS

- Pin and function compatible to the 74F827/8
74FCT827/8 and 74FCT827T/8T
- Industrial temperature -40°C to 85°C
- CMOS power levels: <7.5mW static
- Available in DIP, SOIC, QSOP, ZIP, HQSOP
- Undershoot clamp diodes on all inputs
- TTL-compatible input and output levels
- Ground bounce controlled outputs
- Reduced output swing of 0-3.5V
- Military product compliant to MIL-STD-883, Class B

FCT-T 827T, 828T

- JEDEC-FCT spec compatible
- A, B, and C speed grades with 4.4ns t_{PD} for C
- $I_{OL} = 48\text{mA}$ Ind., 32mA Mil.

FCT-T 2827T, 2828T

- Built-in 25Ω series resistor outputs reduce reflection and other system noise
- A, B, and C speed grades with 4.4ns t_{PD} for C
- $I_{OL} = 12\text{mA}$ Ind.

DESCRIPTION

The QSFCT827T/828T and QSFCT2827T/2828T are 10-bit buffers with three-state outputs that are ideal for driving high-capacitance loads as in memory address and data buses. The 2827/8 are 25Ω resistor output versions useful for driving transmission lines and reducing system noise. The 2827/8 series parts can replace the 827/8 series to reduce noise in an existing design. All inputs have clamp diodes for undershoot noise suppression. All outputs have ground bounce suppression (see QSI Application Note AN-001), and outputs will not load an active bus when V_{CC} is removed from the device.

Figure 1. Functional Block Diagram

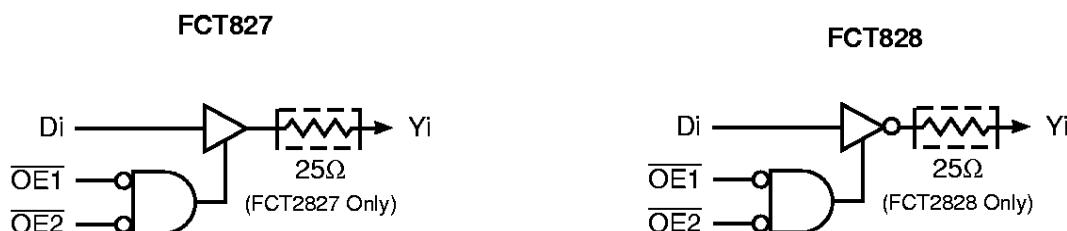


Figure 2. Pin Configurations (All Pins Top View)

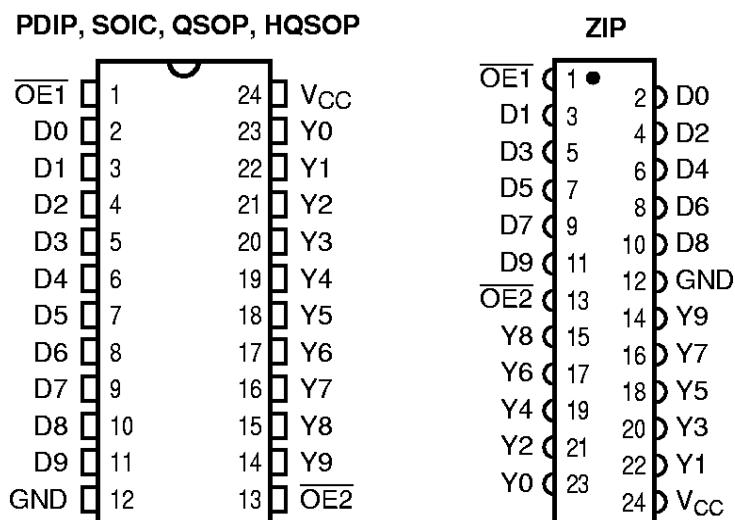


Table 1. Pin Description

Name	I/O	Description
D ₉ -D ₀	I	Data Inputs
Y ₉ -Y ₀	O	Data Outputs
OE _i	I	Output Enables

Table 2. Function Table

Inputs			Outputs		Function
			827, 2827	828, 2828	
OE ₁	OE ₂	Di	Y _i	Ȳ _i	Function
L	L	L	L	H	Enabled
L	L	H	H	L	Enabled
H	—	—	Hi-Z	Hi-Z	High Impedance
—	H	—	Hi-Z	Hi-Z	High Impedance

Table 3. Absolute Maximum Ratings

Supply Voltage to Ground	-0.5V to 7.0V
DC Output Voltage V_{OUT}	-0.5V to 7.0V
DC Input Voltage V_{IN}	-0.5V to 7.0V
AC Input Voltage (for a pulse width $\leq 20\text{ns}$)	-3.0V
DC Input Diode Current with $V_{IN} < 0$	-20mA
DC Output Diode Current with $V_{OUT} < 0$	-50mA
DC Output Current Max. Sink Current/Pin	120mA
Maximum Power Dissipation	0.5 watts
T_{STG} Storage Temperature	-65° to 150°C

Note: Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to QSI devices that result in functional or reliability type failures.

Table 4. Capacitance⁽¹⁾

$T_A = 25^\circ\text{C}$, $f = 1\text{MHz}$, $V_{IN} = 0\text{V}$, $V_{OUT} = 0\text{V}$

Pins ⁽²⁾	SOIC	QSOP	PDIP	ZIP	Unit
1-11, 13-23	8	8	9	10	pF

Notes:

1. Capacitance is characterized but not tested.
2. Pin reference for 24-pin package.

Table 5. Power Supply Characteristics

Symbol	Parameter	Test Conditions ⁽¹⁾	Min	Max	Unit
I_{CC}	Quiescent Power Supply Current	$V_{CC} = \text{Max.}$, freq = 0 $0\text{V} \leq V_{IN} \leq 0.2\text{V}$ or $V_{CC}-0.2\text{V} \leq V_{IN} \leq V_{CC}$	—	1.5	mA
ΔI_{CC}	Supply Current per Input @ TTL HIGH	$V_{CC} = \text{Max.}$, $V_{IN} = 3.4\text{V}$, freq = 0 ⁽²⁾	—	2.0	mA
Q_{CCD}	Supply Current per Input per MHz	$V_{CC} = \text{Max.}$, Outputs open and enabled One bit toggling @ 50% duty cycle Other inputs at GND or $V_{CC}^{(3,4)}$	—	0.25	mA/ MHz

Notes:

1. For conditions shown as Min. or Max., use the appropriate values specified under DC specifications.
2. Per TTL driven input ($V_{IN} = 3.4\text{V}$).
3. For flip-flops, Q_{CCD} is measured by switching one of the data input pins so that the output changes every clock cycle. This is a measurement of device power consumption only and does not include power to drive load capacitance or tester capacitance. This parameter is guaranteed by design but not tested.
4. I_C can be computed using the above parameters as explained in the Technical Overview section.

Table 6. DC Electrical Characteristics Over Operating RangeIndustrial $T_A = -40^\circ\text{C}$ to 85°C , $V_{CC} = 5.0\text{V} \pm 5\%$ Military $T_A = -55^\circ\text{C}$ to 125°C , $V_{CC} = 5.0\text{V} \pm 10\%$

Symbol	Parameter	Test Conditions	Min	Typ ⁽¹⁾	Max	Unit
V_{IH}	Input HIGH Voltage	Logic HIGH for All Inputs	2.0	—	—	V
V_{IL}	Input LOW Voltage	Logic LOW for All Inputs	—	—	0.8	V
ΔV_T	Input Hysteresis	$V_{TLH} - V_{THL}$ for All Inputs	—	0.2	—	V
$ I_{IH} $ $ I_{IL} $	Input Current Input HIGH or LOW	$V_{CC} = \text{Max.}, 0 \leq V_{IN} < V_{CC}$	—	—	5	μA
$ I_{OZ} $	Off-State Output Current (Hi-Z)	$V_{CC} = \text{Max.}, 0 \leq V_{IN} \leq V_{CC}$	—	—	5	μA
I_{OS}	Short Circuit Current (FCTXXX)	$V_{CC} = \text{Max.}, V_{OUT} = \text{GND}^{(2,3)}$	-60	—	—	mA
I_{OR}	Current Drive (FCT2XXX)	$V_{CC} = \text{Max.}, V_{OUT} = 2.0\text{V}^{(3)}$	50	—	—	mA
V_{IC}	Input Clamp Voltage	$V_{CC} = \text{Min.}, I_{IN} = -18\text{mA}, T_A = 25^\circ\text{C}^{(3)}$	—	-0.7	-1.2	V
V_{OH}	Output HIGH Voltage	$V_{CC} = \text{Min.}$ $I_{OH} = -12\text{mA}$ (MIL) $I_{OH} = -15\text{mA}$ (IND)	2.4 2.4	— —	— —	V
V_{OL}	Output LOW Voltage (FCTXXX)	$V_{CC} = \text{Min.}$ $I_{OL} = 32\text{mA}$ (MIL) $I_{OL} = 48\text{mA}$ (IND)	— —	— —	0.50 0.50	V
V_{OL}	Output LOW Voltage (FCT2XXX- 25Ω)	$V_{CC} = \text{Min.}$ $I_{OL} = 12\text{mA}$ (MIL) $I_{OL} = 12\text{mA}$ (IND)	— —	— —	0.50 0.50	V
R_{OUT}	Output Resistance (FCT2XXX- 25Ω)	$V_{CC} = \text{Min.}$ $I_{OL} = 12\text{mA}$ (MIL) $I_{OL} = 12\text{mA}$ (IND)	— 20	25 28	— 40	Ω

Notes:

1. Typical values indicate $V_{CC} = 5.0\text{V}$ and $T_A = 25^\circ\text{C}$.
2. Not more than one output should be shorted and the duration is ≤ 1 second.
3. These parameters are guaranteed by design but not tested.

Table 7. Switching Characteristics Over Operating Range

Industrial $T_A = -40^\circ\text{C}$ to 85°C , $V_{CC} = 5.0\text{V} \pm 5\%$ Military $T_A = -55^\circ\text{C}$ to 125°C , $V_{CC} = 5.0\text{V} \pm 10\%$
 $C_{LOAD} = 50\text{pF}$, $R_{LOAD} = 500\Omega$ unless otherwise noted.

Symbol	Description	827A 828A 2827A 2828A		827B 828B 2827B 2828B		827C 828C 2827C		Unit
		Min	Max	Min	Max	Min	Max	
t_{PHL}	Propagation Delay Di to Yi, 827	Ind Mil	— —	8.0 9.0	— —	5.0 6.5	— —	4.4 5.0
t_{PLH}	Propagation Delay ^(1,2) Di to Yi, 827	Ind Mil	— —	15 17	— —	13 14	— —	10 11
t_{PHL}	Propagation Delay Di to Yi, 2827	Ind Mil	— —	8.0 9.0	— —	5.0 6.5	— —	4.4 5.0
t_{PLH}	Propagation Delay ^(1,2) Di to Yi, 2827	Ind Mil	— —	17 18	— —	— —	— —	ns
t_{PHL}	Propagation Delay Di to Yi, 828	Ind Mil	— —	7.5 9.5	— —	5.0 6.5	— —	4.4 5.0
t_{PLH}	Propagation Delay ^(1,2) Di to Yi, 828	Ind Mil	— —	14 16	— —	13 14	— —	10 11
t_{PHL}	Propagation Delay Di to Yi, 2828	Ind Mil	— —	7.5 9.5	— —	5.0 6.5	— —	ns
t_{PLH}	Propagation Delay ^(1,2) Di to Yi, 2828	Ind Mil	— —	17 18	— —	— —	— —	ns
t_{PZH}	Output Enable Time \overline{OE} to Yi, 827/8	Ind Mil	— —	12 13	— —	8.0 9.0	— —	7.0 8.0
t_{PZL}	Output Enable Time \overline{OE} to Yi, 827/8 ^(1,2)	Ind Mil	— —	23 25	— —	15 16	— —	14 15
t_{PZH}	Output Enable Time \overline{OE} to Yi, 2827/8	Ind Mil	— —	12 13	— —	8.0 9.0	— —	7.0 8.0
t_{PZL}	Output Enable Time \overline{OE} to Yi, 2827/8 ^(1,2)	Ind Mil	— —	23 25	— —	— —	— —	ns
t_{PHZ}	Output Disable Time \overline{OE} to Yi ^(1,3)	Ind Mil	— —	9.0 10	— —	6.0 7.0	— —	5.7 6.7
t_{PLZ}	Output Disable Time ⁽¹⁾ \overline{OE} to Yi	Ind Mil	— —	10 10	— —	7.0 8.0	— —	6.0 7.0

Notes:

1. This parameter is guaranteed by design but not tested.
2. $C_{LOAD} = 300\text{pF}$.
3. $C_{LOAD} = 5\text{pF}$.